

VERSION SHOWING THE CHANGES TO THE CLAIMS

Amend the claims as follows:

1. (Currently amended). An organic logic gate comprising:

    a circuit having an input and an output and comprising at least one organic charging field effect transistor (charging FET) on a substrate;

    the charging FET including a first structured layer comprising source and drain electrodes;

    followed by a semiconductor layer on the electrodes followed by a layer of insulating material on the semiconductor layer and adjacent to and contiguous with a second electrode layer forming a gate electrode; and

    at least one switching organic field effect transistor (switching FET) having at least one gate electrode, a source electrode and a drain electrode;

    the drain-source electrodes of the charging and switching transistors being arranged to be coupled in series between a voltage source and a reference potential such that the gate electrode of the charging FET is not connected via an electrical line directly to a voltage source, to the reference potential, to the input or to the output; wherein the gate electrode of the charging FET is directly capacitively coupled to one of the source/drain electrodes of the charging FET to thereby provide a potential at the gate electrode of the charging FET solely via the capacitive coupling.

Claim 2, canceled.

3. (Previously presented). The organic logic gate as claimed in Claim 1 wherein the capacitive coupling is achieved by the gate electrode of the charging FET overlapping one of the source/drain electrodes of the charging FET.

Claims 4-7, canceled.

8. (Previously presented) The organic logic gate as claimed in Claim 1 wherein the organic logic gate is constructed without plated-through holes.